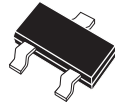


CMPTA29
HIGH VOLTAGE
NPN SILICON
DARLINGTON TRANSISTOR



SOT-23 CASE

CentralTM

Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPTA29 is an NPN silicon darlington transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for applications requiring extremely high voltage and high gain.

MARKING CODE: C29

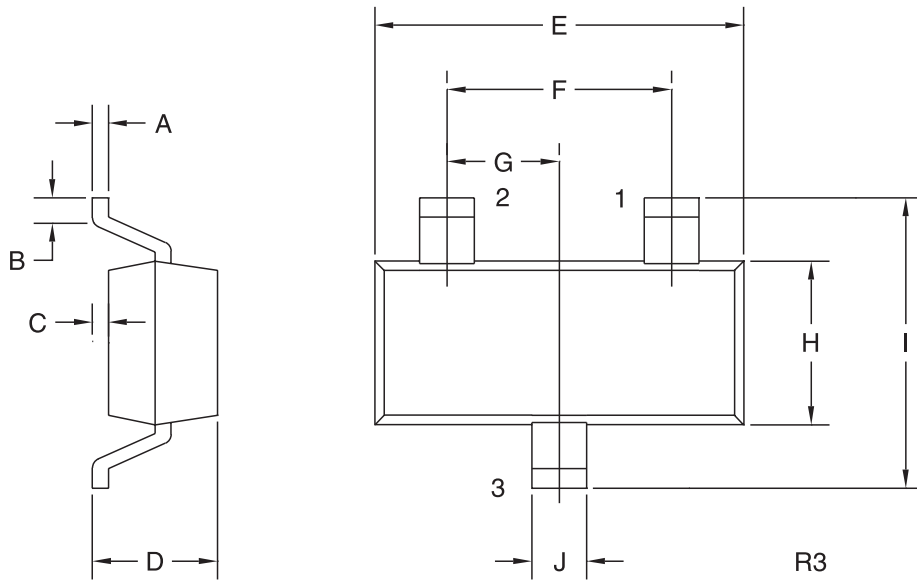
MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CES}	100	V
Emitter-Base Voltage	V_{EBO}	12	V
Continuous Collector Current	I_C	500	mA
Power Dissipation	P_D	350	mW
Operating and Storage			
Junction Temperature	T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
Thermal Resistance	θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$) unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CES}	$V_{CE}=80\text{V}$		500	nA
I_{CBO}	$V_{CB}=80\text{V}$		100	nA
I_{EBO}	$V_{BE}=10\text{V}$		100	nA
BV_{CES}	$I_C=100\mu\text{A}$	100		V
BV_{CBO}	$I_C=100\mu\text{A}$	100		V
BV_{EBO}	$I_E=10\mu\text{A}$	12		V
$V_{CE(SAT)}$	$I_C=10\text{mA}, I_B=10\mu\text{A}$		1.2	V
$V_{CE(SAT)}$	$I_C=100\text{mA}, I_B=100\mu\text{A}$		1.5	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$		2.0	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	10,000		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=100\text{mA}$	10,000		
f_T	$V_{CE}=5.0\text{V}, I_C=10\text{mA}, f=100\text{MHz}$	125		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		8.0	pF

SOT-23 CASE - MECHANICAL OUTLINE



LEAD CODE:

- 1) BASE
- 2) EMITTER
- 3) COLLECTOR

MARKING CODE: C29

SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.003	0.007	0.08	0.18
B	0.006	-	0.15	-
C	-	0.005	-	0.13
D	0.035	0.043	0.89	1.09
E	0.110	0.120	2.80	3.05
F	0.075		1.90	
G	0.037		0.95	
H	0.047	0.055	1.19	1.40
I	0.083	0.098	2.10	2.49
J	0.014	0.020	0.35	0.50

SOT-23 (REV: R3)